CBCS	SGI	
		MARKET BY STREET

Spinivas Institute of Technolog,

USN

18EC33

Third Semester B.E. Degree Examination, July/August 2021 Electronic Devices

Time: 3 hrs.

Max. Marks: 100

Note: Answer any	FIVE full	questions.
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1	a.	What are the different types of Bonding Forces in solids and explain any one.	(06 Marks)
	b.	Draw the typical band structures at OK for insulator, semiconductor and metal a	nd explain
		it.	(06 Marks)
	c.	With mathematical equations, describe the hall effect.	(08 Marks)
2	a.	Explain Electron-hole pair in a semiconductor with the help of the graph.	(06 Marks)
-	b.	Explain the effects of temperature and doping on mobility.	(06 Marks)
	c.	Describe the drift of electrons and holes in a semiconductor bar.	(08 Marks)
3	a.	Draw the I-V characteristic of a Pn-junction with current equation under ed	quilibrium,
3		forward and reverse bias and explain it.	(06 Marks)
	b.	Explain the concept of Zener breakdown with energy band diagram.	(06 Marks)
	c.	Explain the solar cells with structures.	(08 Marks)
		Draw the piece wise linear approximations of junction diode characteristics for i	deal diode.
4	a.	ideal diode with offset voltage and ideal diode with offset voltage and resistance.	(06 Marks)
		ideal diode with offset voltage and ideal diode with offset voltage and resistance.	(06 Marks)
	b.	Draw the schematic representation of a P-i-n photodiode and explain it.	(08 Marks)
	C.	Explain the Avalanche Breakdown with energy diagram.	
5	a.	Explain the working of P-n-P device and also draw the curve of Ic versus V _{BC} .	(06 Marks)
	b.	Describe the various mechanisms of a switching cycle of a PnP transistor.	(06 Marks)
	c.	Write the step-by-step fabrication of a BJT with diagrams.	(08 Marks)
6	a.	Define the following parameters:	
		i) Emitter injection efficiency	
		ii) Current transfer ratio	
		iii) Base to collector current amplification factor.	(06 Marks)
	b.	Draw the simple switching circuit of PnP transistor and explain it.	(06 Marks)
	c.	Discuss Base Narrowing in PnP transistor.	(08 Marks)
	d Alba	Dec 1 : P. TEFE 6 different coto voltage	(10 Marks)
7	a.	Explain the operation of a basic Pn JFET for different gate voltage.	(10 Marks)
	b.	Draw the small signal equivalent circuit of JFET and explain it.	
8	a.	Draw the energy band diagram of an two terminal MOS capacitor with a P-type s	ubstrate for
U	۳.	a negative gate bias and a moderate positive gate bias and explain it.	(10 Marks)
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	Ů.		(10 Marks)
^		Describe the Rapid thermal processing with the help of diagram.	(10 Marks)
9	a.		(10 Marks)
	b.		
10	a.	What are the types of integrated circuits and explain it.	(06 Marks)
500.00	b.	Mention the Advantages of Integration.	(06 Marks)
	c.	contains of CMOS inverter	(08 Marks)

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